# PMPB33XN

## 30 V single N-channel Trench MOSFET

6 July 2012

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Trench MOSFET technology
- Very fast switching
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

#### 1.3 Applications

- · Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portables
- Hard disk and computing power management

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	5.5	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; $I_{D}$ = 4.3 A; $T_{j}$ = 25 °C		-	37	47	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





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## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D
2	D	drain	7 7	
3	G	gate		G T T
4	S	source	3 8 4	\$ 017aaa253
5	D	drain	Transparent top view	077444256
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

## 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB33XN	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PMPB33XN	1P

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	5.5	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	4.3	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	2.7	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	17	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.5	W
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Symbol	Parameter	Conditions		Min	Max	Unit	
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	2.4	W	
		T <sub>sp</sub> = 25 °C		-	8.3	W	
T <sub>j</sub>	junction temperature			-55	150	°C	
T <sub>amb</sub>	ambient temperature			-55	150	°C	
T <sub>stg</sub>	storage temperature			-65	150	°C	
Source-drain diode							
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.7	Α	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

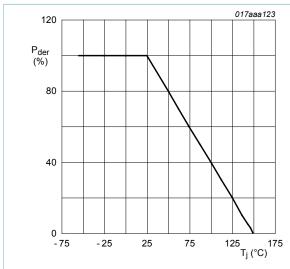


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

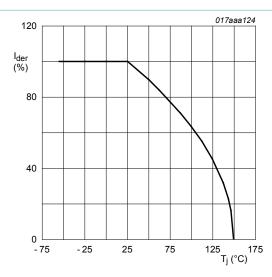


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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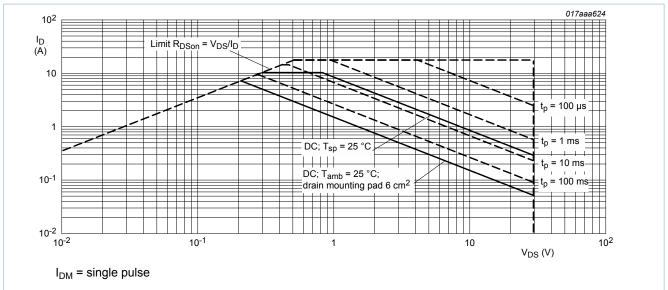


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
from	thermal resistance	in free air	[1]	-	245	280	K/W
	from junction to ambient		<u>[2]</u>	-	74	85	K/W
	ambient		[3]	-	45	52	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	10	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm $^2$ , t  $\leq$  5 s

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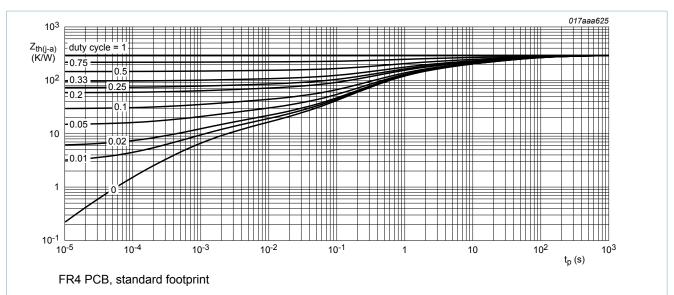


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

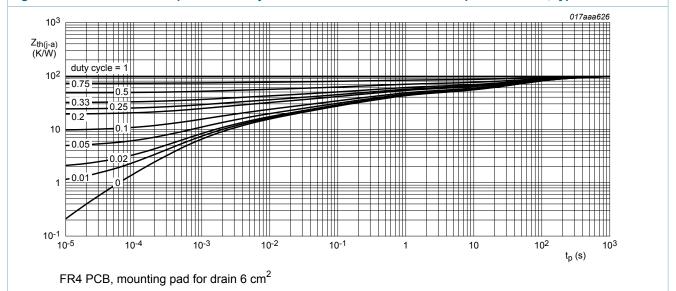


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					_
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	0.45	0.8	1.2	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	1	μA
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	100	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 4.5 V; $I_{D}$ = 4.3 A; $T_{j}$ = 25 °C	-	37	47	mΩ
	resistance	$V_{GS}$ = 4.5 V; $I_D$ = 4.3 A; $T_j$ = 150 °C	-	63	80	mΩ
		$V_{GS}$ = 2.5 V; $I_D$ = 1 A; $T_j$ = 25 °C	-	55	76	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 4.3 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	20	-	S
$R_G$	gate resistance	f = 1 MHz	-	9.8	-	Ω
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 4.3 A; $V_{GS}$ = 4.5 V; $T_{j}$ = 25 °C	-	5.1	7.6	nC
Q <sub>GS</sub>	gate-source charge		-	1	-	nC
$Q_{GD}$	gate-drain charge		-	1.3	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 15 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	505	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	57	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	48	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $I_{D}$ = 4.3 A; $V_{GS}$ = 4.5 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	17	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	21	-	ns
t <sub>f</sub>	fall time		-	20	-	ns
Source-dra	nin diode		'			,
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 1.7 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.8	1.2	V

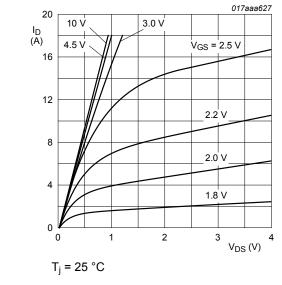


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

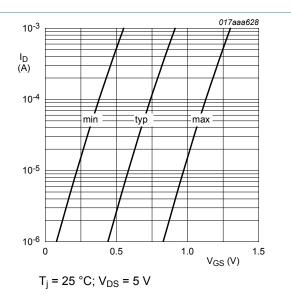


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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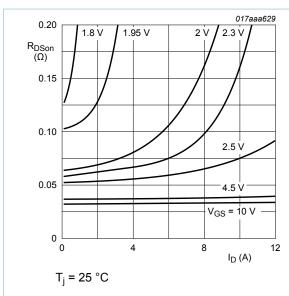


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

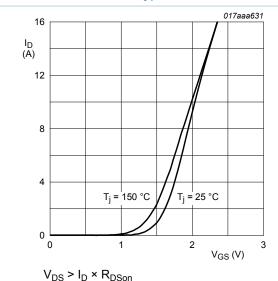


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

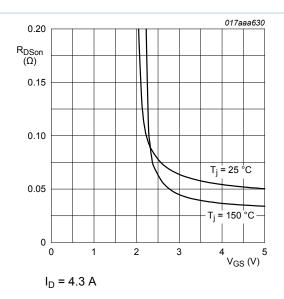


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

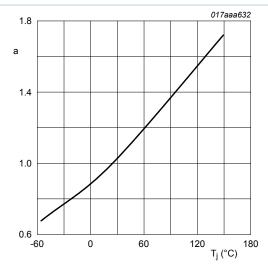


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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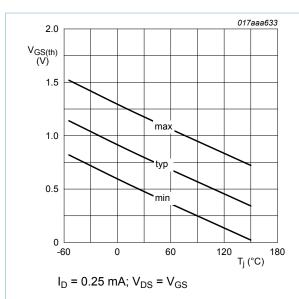


Fig. 12. Gate-source threshold voltage as a function of junction temperature

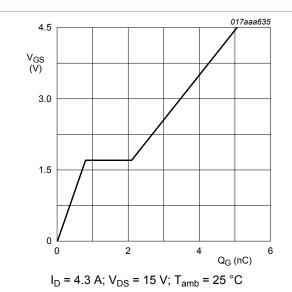


Fig. 14. Gate-source voltage as a function of gate charge; typical values

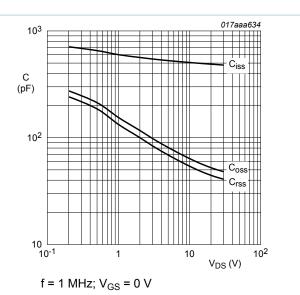


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

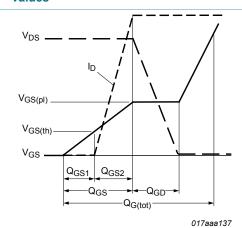
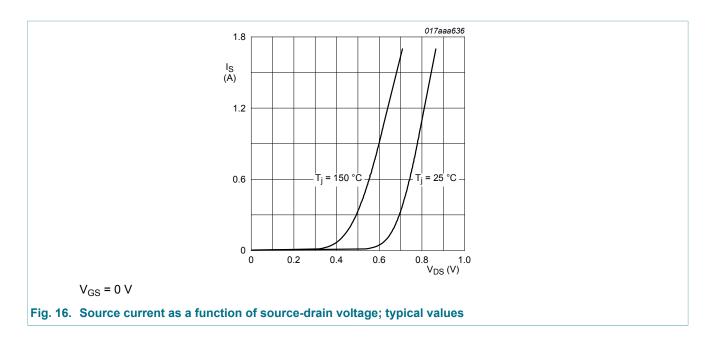
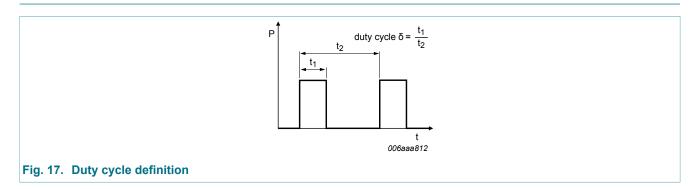


Fig. 15. Gate charge waveform definitions

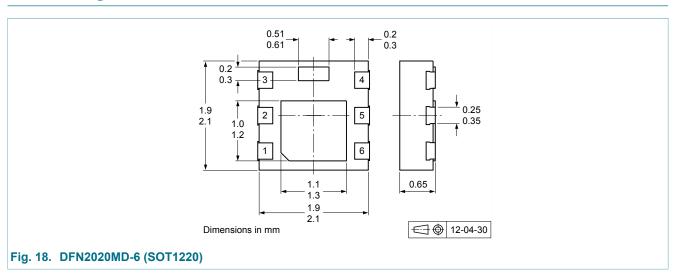
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### 8. Test information



## 9. Package outline



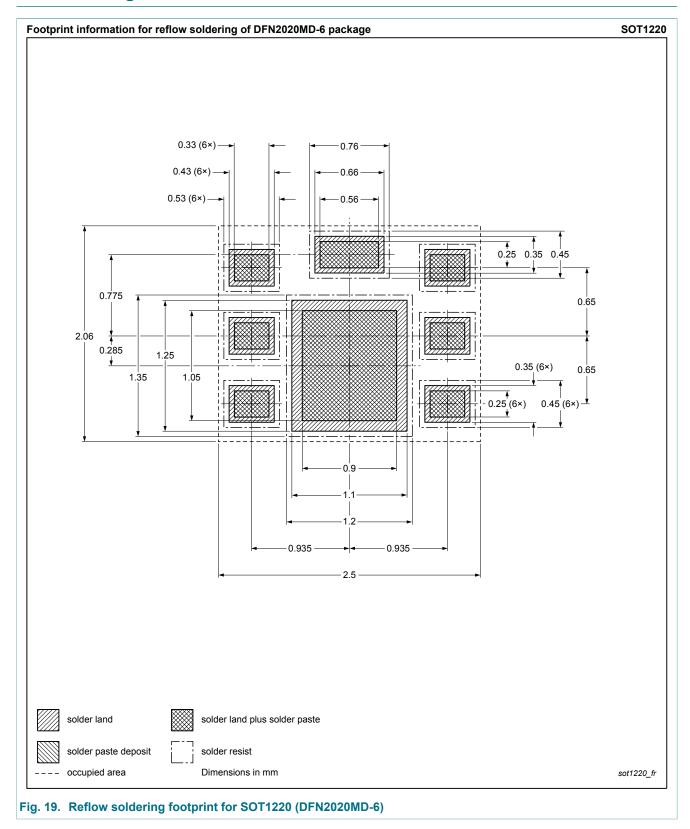
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### 10. Soldering



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## 11. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB33XN v.1	20120706	Product data sheet	-	-

#### 30 V single N-channel Trench MOSFET

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